



1H1G THRU 1H8G

High Efficient Rectifier

Features

- High efficiency
- High current capability
- High Reliability
- High surge current capability
- Glass passivated chip junction
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Mechanical Data

Package: R-1

Molding compound

A

	FSM	A	30		
Forward Surge Current (Non-repetitive) @ 1ms, square wave, 1 cycle, Tj=25			60		
Current squared time @ 1ms t8.3 ms Tj=25 Rating of per diode	I ² t	A ² s	3.735		
Typical junction capacitance @ Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	Cj	pF	15	13	8
Storage Temperature	Tstg		-55 ~ +150		
Junction Temperature	Tj		-55 ~ +150		

Electrical Characteristics Ta=25 Unless otherwise specified

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	1H1G	1H2G	1H3G	1H4G	1H5G	1H6G	1H7G	1H8G
Maximum instantaneous forward voltage drop per diode	VF	V	IFM=1.0A	1.0			1.3		1.7		
Maximum DC reverse current at rated DC blocking voltage per diode	IR	μA	Tj=25								

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Outline Dimensions



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